

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A thin film transistor, comprising:  
a gate electrode having a gate insulation film;  
channel regions that extend through the gate insulation film in the gate electrode; and  
source drain regions connected to said channel regions that are formed against a semiconductor film that is formed on the surface of an insulation substrate, wherein recombination centers which capture carriers are formed in said channel regions by part of crystal semiconductor films having a relatively low degree of crystallization among crystal semiconductor films that form said channel regions.
2. (Previously Presented) The thin film transistor of Claim 1, wherein said recombination centers are concentrated adjacent to said drain regions within said channel regions.
3. (Previously Presented) The thin film transistor of Claim 2, wherein said recombination centers are concentrated in a region, among channel regions, whose distance from the drain regions is equivalent to  $1/3$  to  $1/10$  of a channel length.
4. (Previously Presented) The thin film transistor according to Claim 1, wherein regions, among said channel regions, in which said recombination centers are concentrated have different film thickness compared to other regions.
5. (Previously Presented) The thin film transistor according to Claim 1, wherein regions, among said channel regions, in which said recombination centers are concentrated have different surface positions compared to other regions.

6. (Previously Presented) The thin film transistor of Claim 5, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different surface height positions compared to other regions due to a different thickness of the semiconductor films forming said channel regions.

7. (Previously Presented) The thin film transistor of Claim 5, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different surface height positions compared to other regions due to the formation of at least one of indented sections and bulged sections in a lower layer of the semiconductor films forming said channel regions.

8. (Withdrawn) A method for manufacturing a thin film transistor comprising a gate electrode having a gate insulation film, channel regions that extend through a gate insulation film in the gate electrode, and source drain regions connected to said channel regions that are formed against a semiconductor film being formed on a surface of an insulation substrate, wherein a section having a relatively low degree of crystallization is formed within a predetermined region of said semiconductor films by applying laser annealing to said semiconductor films after forming the semiconductor films that form said channel regions.

9. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 8, wherein a section with a relatively low degree of crystallization is formed in the predetermined regions of said semiconductor film by applying said laser annealing to said semiconductor film after forming the semiconductor films with partially different film thickness as semiconductor films that form said channel regions.

10. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 8, wherein a section with a relatively low degree of crystallization is formed in the predetermined regions to said semiconductor film by applying said laser annealing for said

semiconductor film after forming the semiconductor films with different surface height positions as semiconductor films that form said channel regions.

11. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 10, wherein the thickness of said semiconductor film is made to be different partially in forming said semiconductor film with different surface height positions.

12. (Withdrawn) The method for manufacturing a thin film transistor according to Claim 11, wherein at least one of an indented section and a bulging section is formed beforehand in a lower layer of said semiconductor films in forming said semiconductor films with different surface height positions.

13. (Previously Presented) The thin film transistor according to Claim 2, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different film thickness compared to other regions.

14. (Previously Presented) The thin film transistor according to Claim 3, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different film thickness compared to other regions.

15. (Previously Presented) The thin film transistor according to Claim 2, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different surface positions compared to other regions.

16. (Previously Presented) The thin film transistor according to Claim 3, wherein the regions, among said channel regions, in which said recombination centers are concentrated have different surface positions compared to other regions.

17. (Previously Presented) A display device having a thin film transistor, the thin film transistor comprising:

a gate electrode having a gate insulation film;

channel regions that extend through the gate insulation film in the gate electrode; and

source drain regions connected to said channel regions that are formed against a semiconductor film that is formed on the surface of an insulation substrate, wherein recombination centers which capture carriers are formed in said channel regions by part of crystal semiconductor films having a relatively low degree of crystallization among crystal semiconductor films that form said channel regions.

18. (Withdrawn) A method for manufacturing a display device having a thin-film transistor, the thin-film transistor comprising a:

gate electrode having a gate insulation film, channel regions that extend through a gate insulation film in the gate electrode, and source drain regions connected to said channel regions that are formed against a semiconductor film being formed on a surface of an insulation substrate, wherein a section having a relatively low degree of crystallization is formed within a predetermined region of said semiconductor films by applying laser annealing to said semiconductor films after forming the semiconductor films that form said channel regions.

19. (Currently Amended) A thin-film transistor, comprising:

a channel region facing a gate electrode ~~through a gate insulating film~~, the channel region having a partially distorted portion distorted in a thickness direction of the channel region;

source and drain regions connection to the channel region in a semiconductor film in contact with a surface of an insulating substrate;

a gate insulating film formed at least over the channel, source, and drain regions; and

a recombination center formed around the partially distorted portion, the recombination center having a relatively low degree of crystallization among crystal semiconductor films forming the channel region.